SGS-THOMSON MICROELECTRONICS

ESM 765PI-600/800

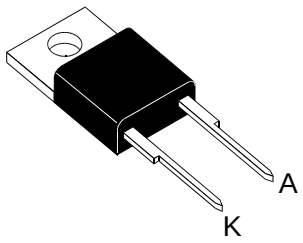
FAST RECOVERY RECTIFIER DIODES

- HIGH VOLTAGE CAPABILITY
- FAST AND SOFT RECOVERY
- THE SPECIFICATIONS AND CURVES ENABLE THE DETERMINATION OF THE t_{rr} AND I_{RM} AT 100 °C UNDER USERS CONDITIONS
- INSULATED

APPLICATIONS

- MOTOR CONTROLS AND CONVERTERS
- SWITCH MODE POWER SUPPLIES

Insulting voltage 2500 V_{RMS}



Isolated
TO220AC
(Plastic)

DESCRIPTION

Fast recovery rectifiers suited for applications in combination with superswitch transistors.

ABSOLUTE MAXIMUM RATINGS (limiting values)

Symbol	Parameter		Value	Unit
I_{FRM}	Repetitive Peak Forward Current	$t_p \leq 20\mu s$	120	A
$I_{F\ (RMS)}$	RMS Forward Current		16	A
$I_{F\ (AV)}$	Average Forward Current	$T_C = 100°C$ $\delta = 0.5$	10	A
I_{FSM}	Surge non Repetitive Forward Current	$t_p = 10ms$ Sinusoidal	120	A
P_{tot}	Power Dissipation	$T_C = 100°C$	20	W
T_{stg} T_j	Storage and Junction Temperature Range		- 40 to + 150 - 40 to + 150	°C

Symbol	Parameter	ESM 765PI-		Unit
		600	800	
V_{RRM}	Repetitive Peak Reverse Voltage	600	800	V
V_{RSM}	Non Repetitive Peak Reverse Voltage	600	800	V

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th\ (j-c)}$	Junction-case	3.5	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I_R	T_j = 25°C	$V_R = V_{RRM}$			20	µA
	T_j = 100°C				1	mA
V_F	T_j = 25°C	I_F = 10A			1.4	V
	T_j = 100°C				1.35	

RECOVERY CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
t_{rr}	T_j = 25°C V_R = 30V	I_F = 1A	dI_F/dt = - 15A/µs			300	ns
Q_{rr}	T_j = 25°C V_R = 200V	I_F = 10A	dI_F/dt = - 50A/µs		2.3		µC

To evaluate the conduction losses use the following equations :

$V_F = 1.2 + 0.015\ I_F$ $\quad P = 1.2 \times I_{F(AV)} + 0.015\ I_F{}^2{}_{(RMS)}$

Figure 1. Low frequency power losses versus average current

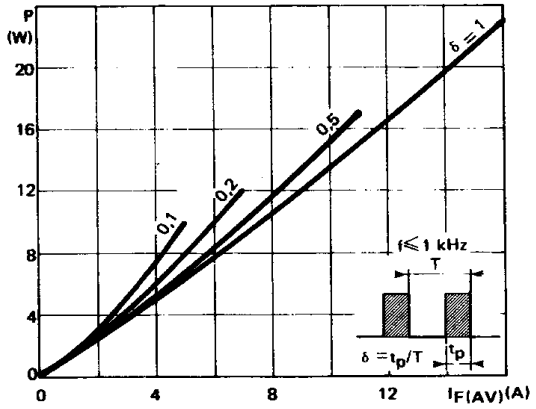


Figure 2. Peak current versus form factor

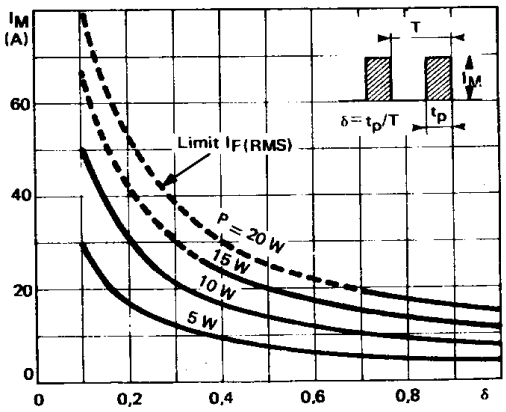


Figure 3. Non repetitive peak surge current versus overload duration

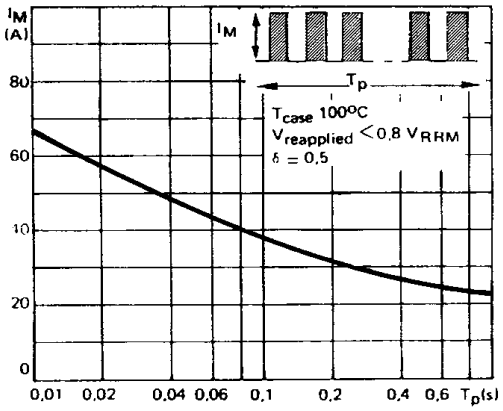


Figure 4. Thermal impedance versus pulse width

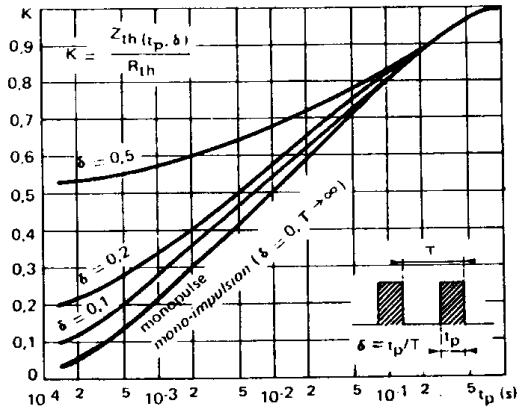


Figure 5. Voltage drop versus forward current

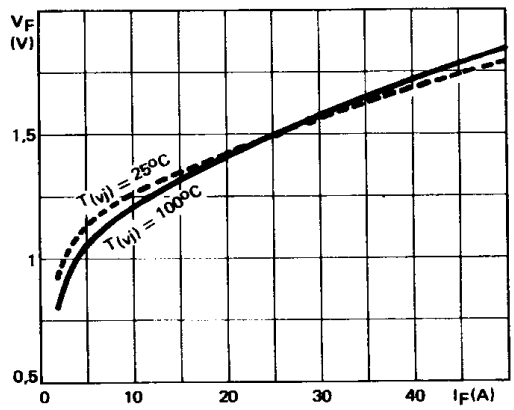


Figure 6. Capacitance versus applied reverse voltage

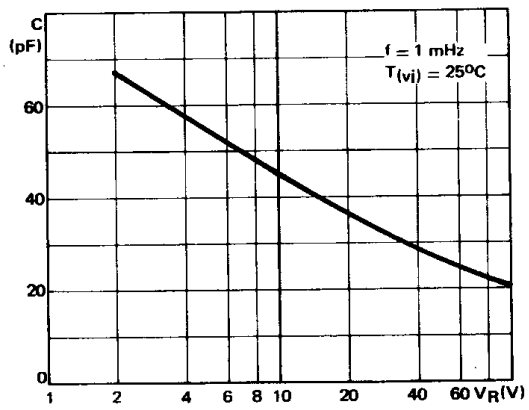


Figure 7. Recovery charge versus di_F/dt

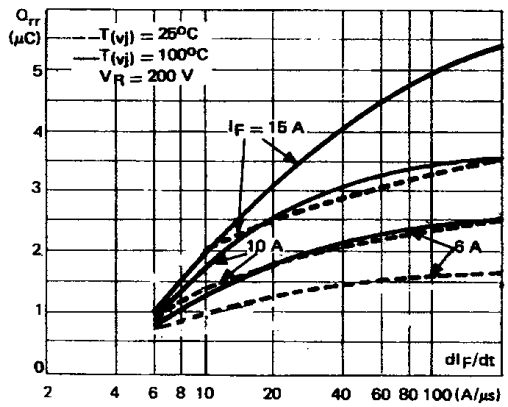


Figure 8. Recovery time versus di_F/dt

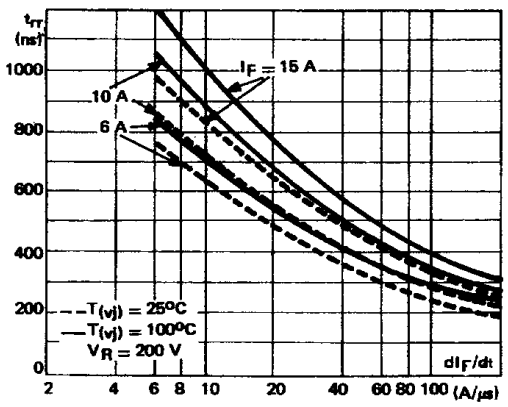
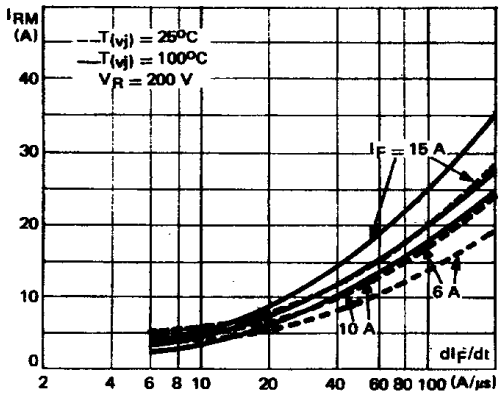
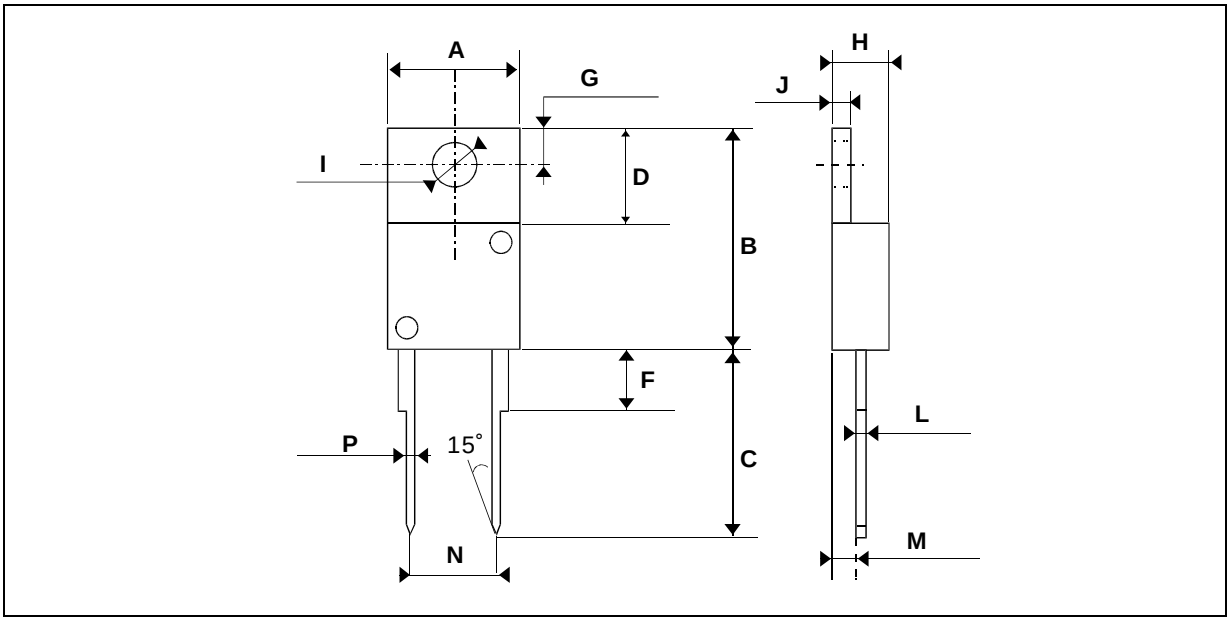


Figure 9. Peak reverse current versus di_F/dt



PACKAGE MECHANICAL DATA

Isolated TO220AC Plastic



Note: SGS-THOMSON reserves the right to have two notches on the heatsink.

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	10.20	10.50	0.401	0.413
B	14.23	15.87	0.560	0.625
C	12.70	14.70	0.500	0.579
D	5.85	6.85	0.230	0.270
F		4.50		0.178
G	2.54	3.00	0.100	0.119
H	4.48	4.82	0.176	0.190
I	3.55	4.00	0.140	0.158
J	1.15	1.39	0.045	0.055
L	0.35	0.65	0.013	0.026
M	2.10	2.70	0.082	0.107
N	4.58	5.58	0.18	0.22
P	0.64	0.96	0.025	0.038

Cooling method : by conduction (method C)
Marking : type number
Weight : 2g
Recommended torque value : 80cm. N
Maximum torque value : 100cm. N

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